Product data sheet

1. Product profile

1.1 General description

Ultrafast epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristic
- Low forward voltage drop
- Low thermal resistance
- Isolated package

1.3 Applications

- High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)Power Factor Correction (PFC)

1.4 Quick reference data

- V_{RRM} ≤ 600 V
- V_F ≤ 1.11 V

- $I_{F(AV)} \leq 5 A$
- $t_{rr} \le 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode (k)		
2	anode (a)	mb	k - - - - - - - -
mb	mounting base; isolated		
		SOD113 (2-lead TO-220	OF)



3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BYV25X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113			

4. Limiting values

Table 3. Limiting values

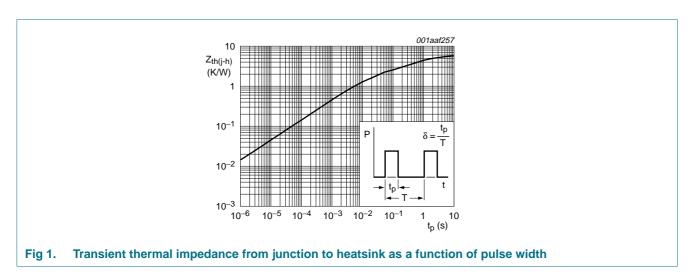
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_h \le 100~^{\circ}C$	-	600	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_h \le$ 115 °C	-	5	Α
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_h \le$ 115 °C	-	10	Α
I _{FSM}	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	60	Α
current	current	t = 8.3 ms; sinusoidal waveform	-	66	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	5.5	K/W
		without heatsink compound	-	-	5.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

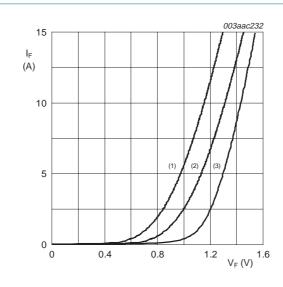
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz; sinusoidal waveform; relative humidity $\leq 65 \%$; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 6. Characteristics

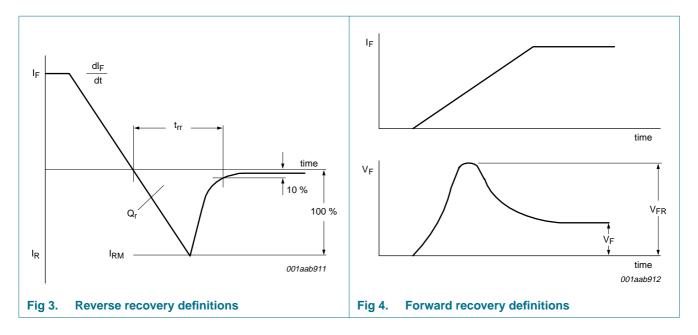
 $T_i = 25 \,^{\circ}C$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	$I_F = 5 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	0.97	1.11	V
		I _F = 5 A	-	1.12	1.30	V
I _R	reverse current	V _R = 600 V	-	2	50	μΑ
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.1	0.35	mA
Dynamic o	haracteristics					
Q _r	recovered charge	I_F = 2 A to V_R \geq 30 V; dI_F/dt = 20 A/ μ s; see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s}; \text{ see } \underline{\text{Figure 3}}$	-	50	60	ns
I _{RM}	peak reverse recovery current	I_F = 10 A to V_R \geq 30 V; dI_F/dt = 50 A/ μ s; T_j = 100 °C; see Figure 3	-	3	5.5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; see Figure 4	-	3.2	-	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_i = 150 \,^{\circ}\text{C}$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage



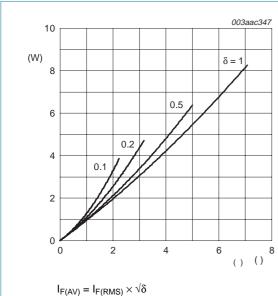


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values

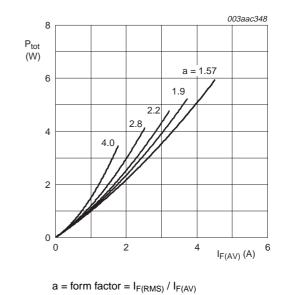
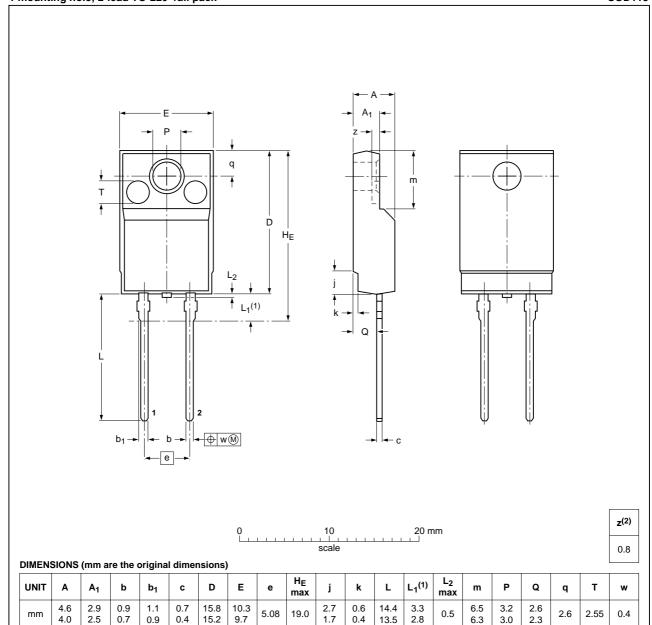


Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

SOD113



Notes

- 1. Terminals are uncontrolled within zone L_1 .
- 2. z is depth of T.

OUTLINE		REFER	ENCES	EUROPEAN			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOD113		2-lead TO-220F				02-04-09 07-06-18	

Fig 7. Package outline SOD113 (2-lead TO-220F)

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9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25X-600_1	20080812	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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12. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data1
2	Pinning information 1
3	Ordering information
4	Limiting values
5	Thermal characteristics 3
6	Isolation characteristics
7	Characteristics 4
8	Package outline 6
9	Revision history 7
10	Legal information 8
10.1	Data sheet status 8
10.2	Definitions 8
10.3	Disclaimers
10.4	Trademarks 8
11	Contact information 8
12	Contents

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